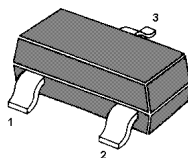


TRANSISTOR (PNP)

SOT-23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

MARKING: 2T1

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

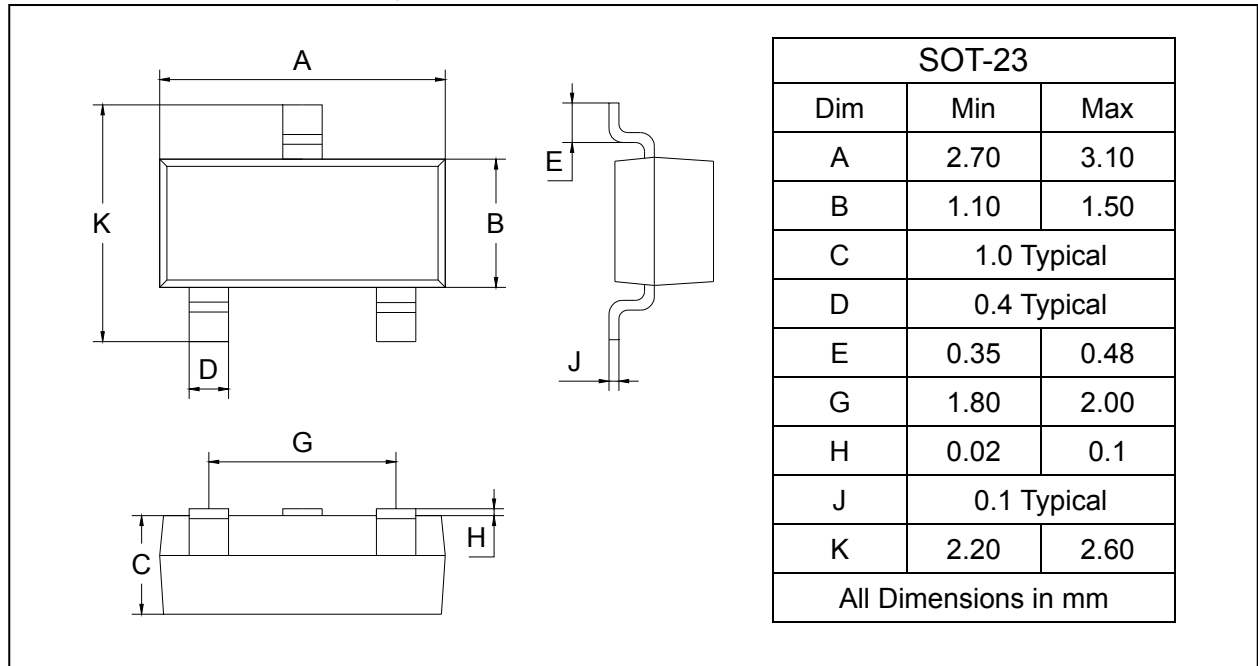
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	416	$^{\circ}\text{C/W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

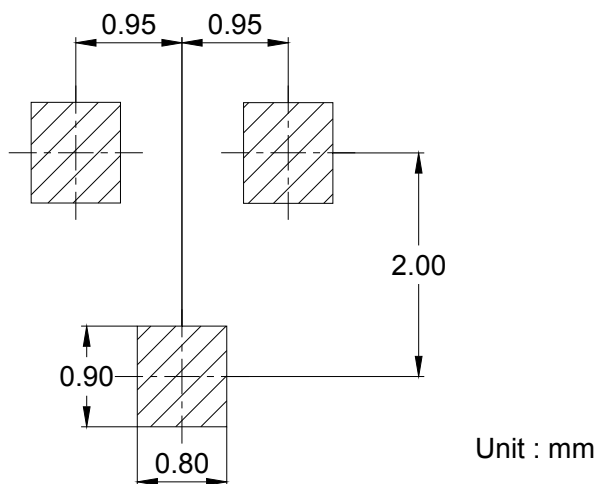
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1\text{mA}, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40\text{V}, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20\text{V}, I_B=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-1\text{V}, I_C=-50\text{mA}$	120		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE}=-6\text{V}, I_C=-20\text{mA}, f=30\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$			5	pF

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



Typical Characteristics

